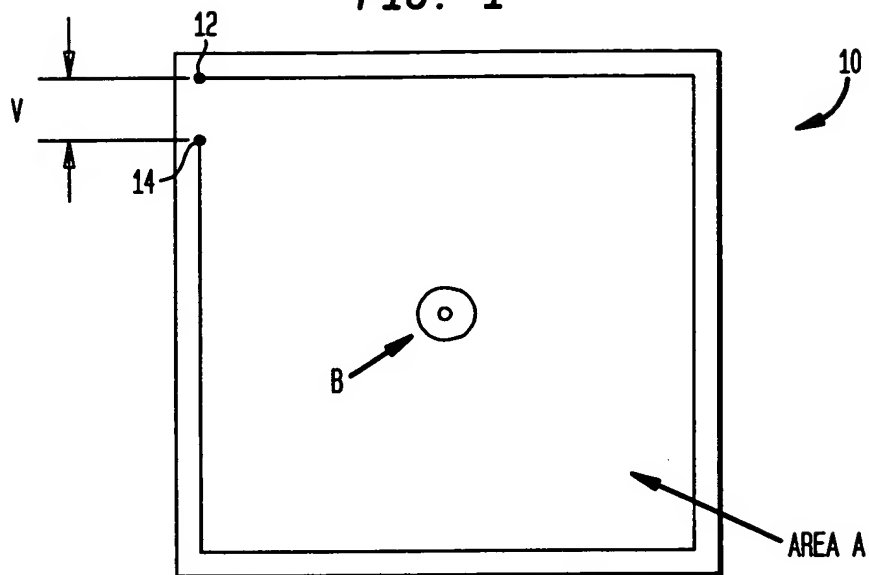
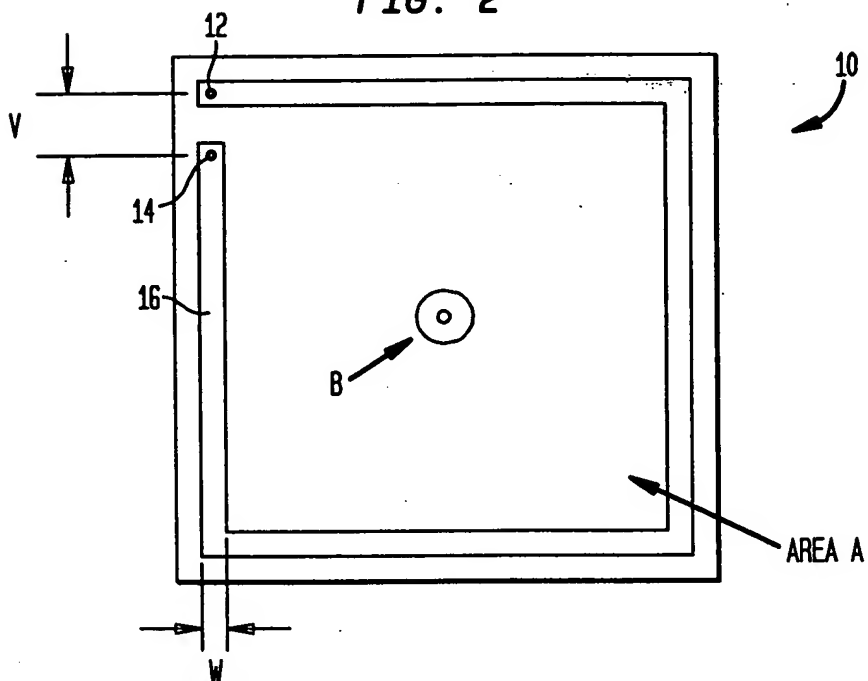


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**FIG. 1****FIG. 2**

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FIG. 3

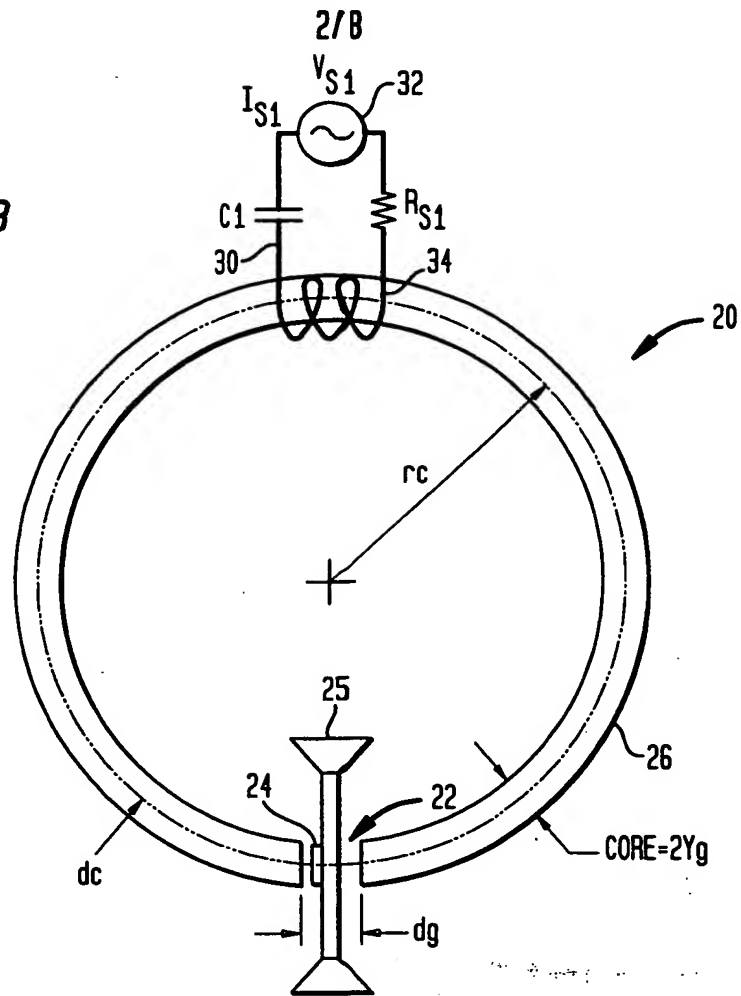


FIG. 3A

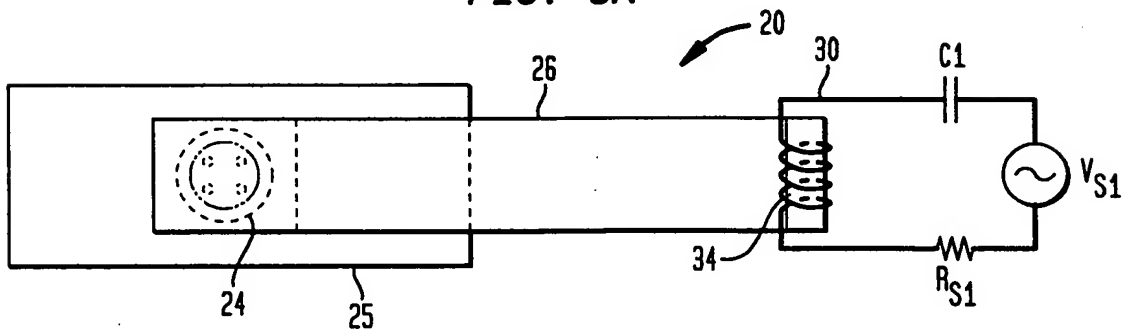
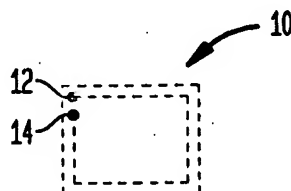


FIG. 3B



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FIG. 3C

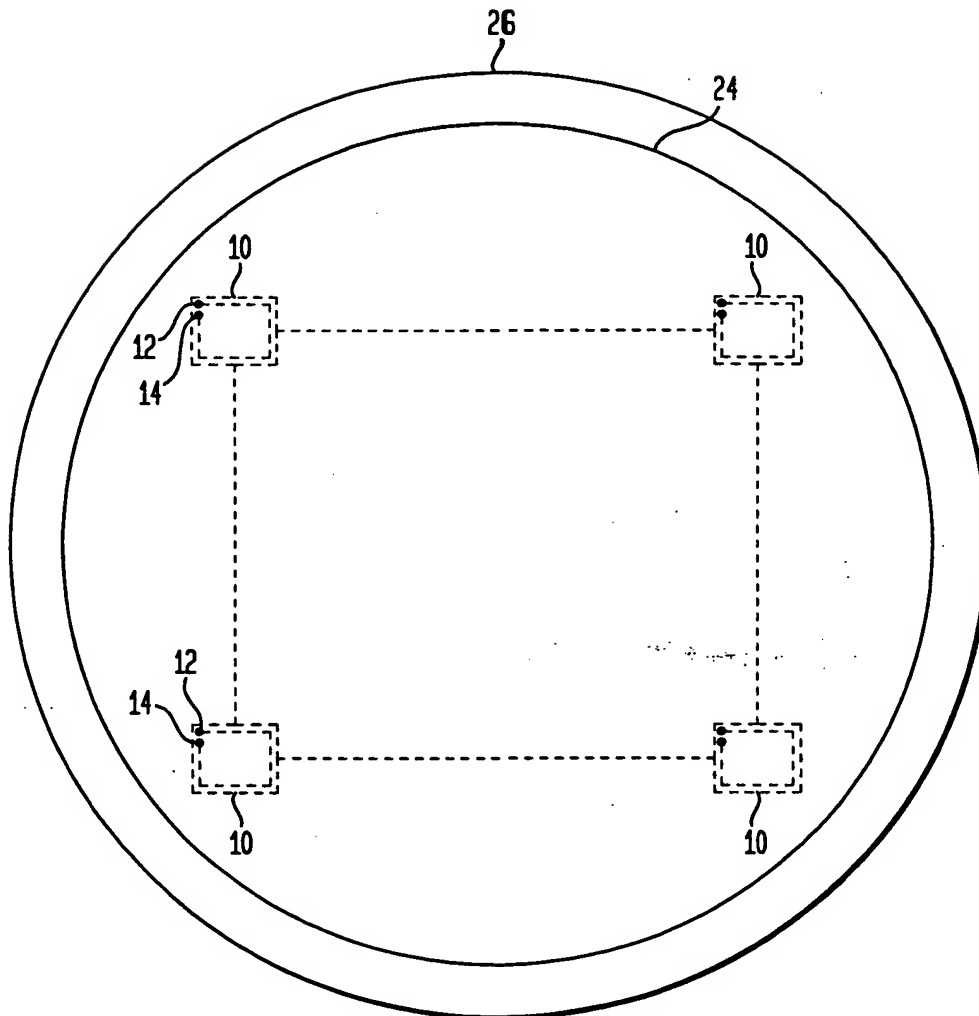


FIG. 4

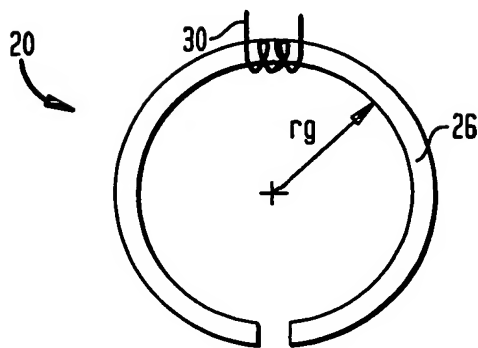
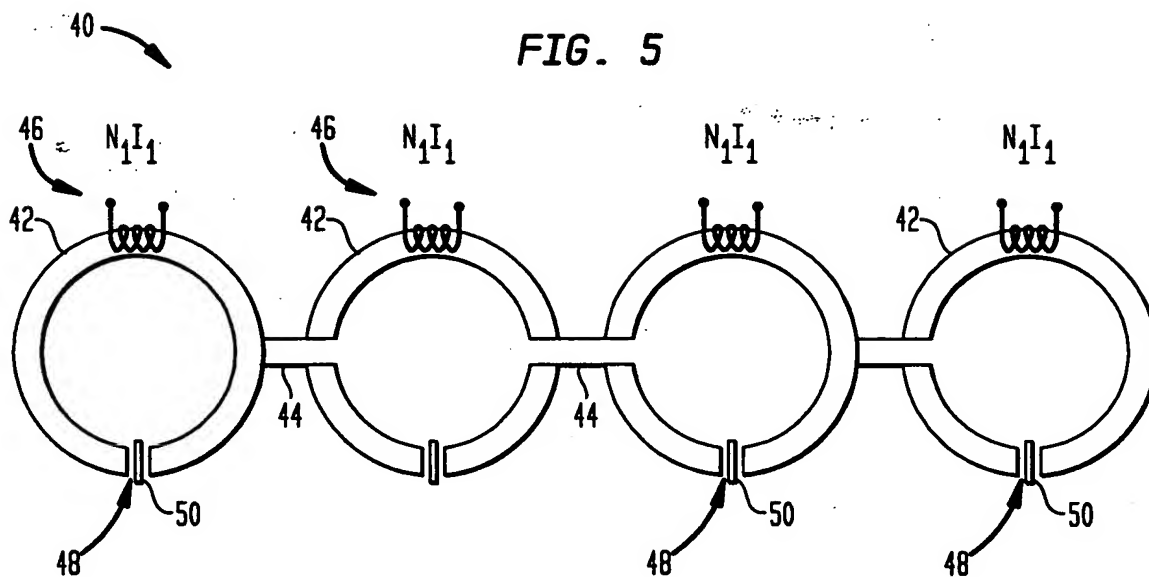


FIG. 5



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FIG. 6

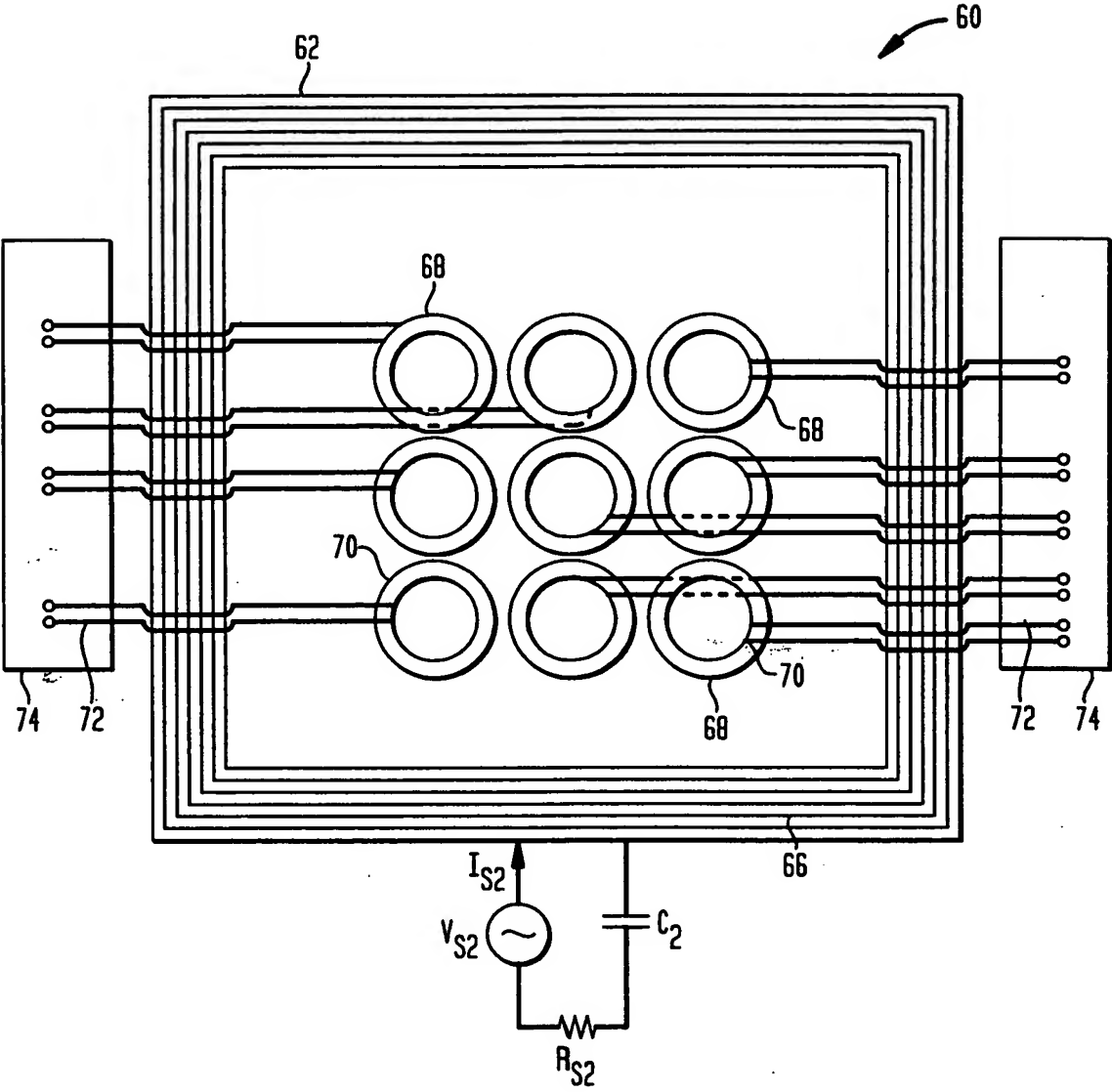


FIG. 7

The diagram shows a semiconductor device with three main regions labeled $P-S_x$. Each region has two N^+ contacts at the top corners. The top region is connected to a **GATE PAD** on its left and a **DIFFUSION PAD** on its right. The middle region is connected to a **DIFFUSION PAD** on its left and a **DIFFUSION PAD** on its right. The bottom region is connected to a **DIFFUSION PAD** on its left and a **DIFFUSION PAD** on its right. A dashed line labeled **TO GROUND** connects the top region to the bottom region. A circular symbol labeled **B** is located in the upper right corner. A vertical arrow labeled **V** points downwards from the top right corner.

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FIG. 8

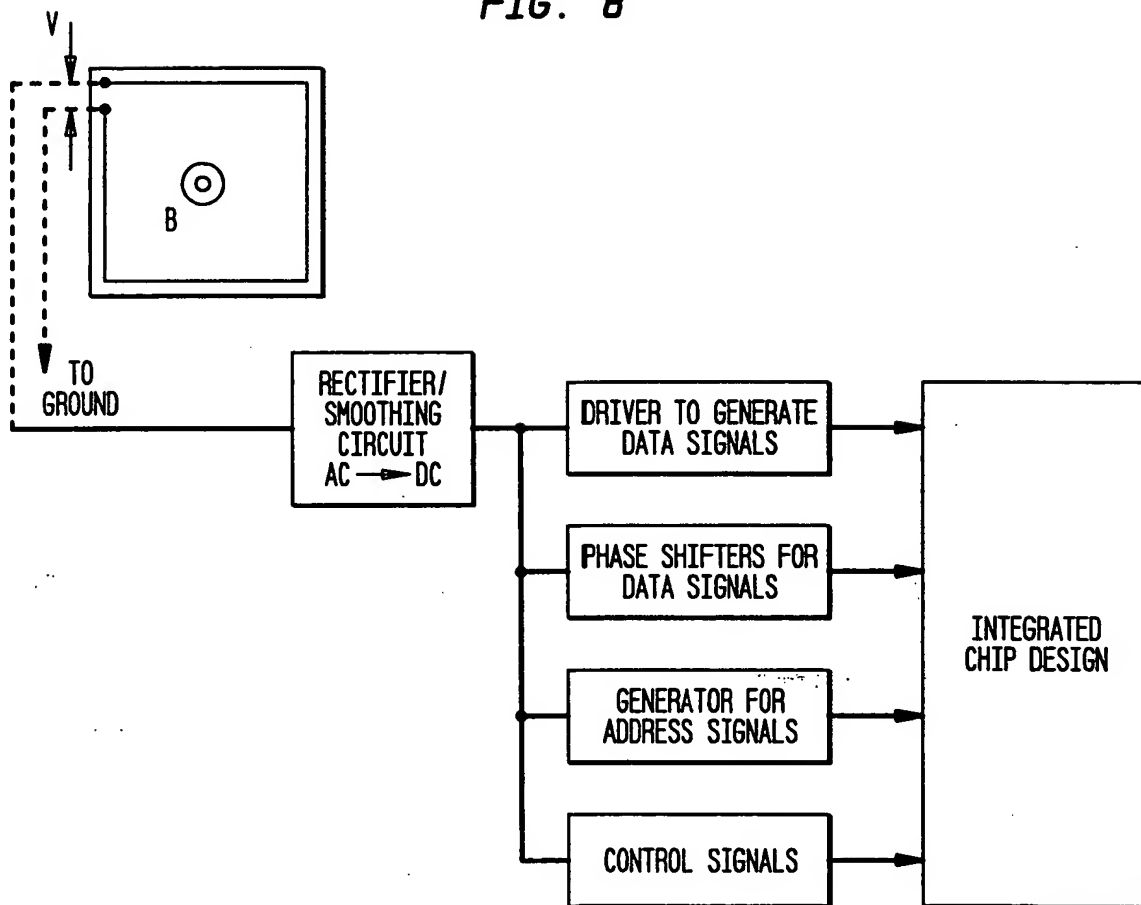


FIG. 9

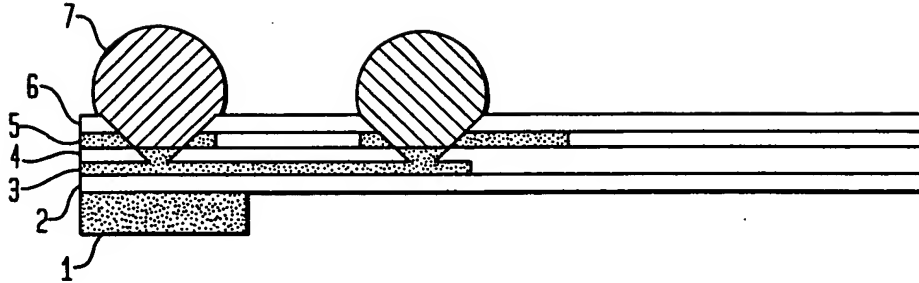


FIG. 10

